To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SB860

Silicon PNP Triple Diffused

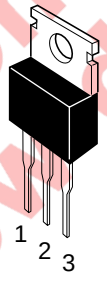
ADE-208-861 (Z)
1st. Edition
September 2000

Application

Low frequency power amplifier TV vertical deflection output complementary pair with 2SD1137

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

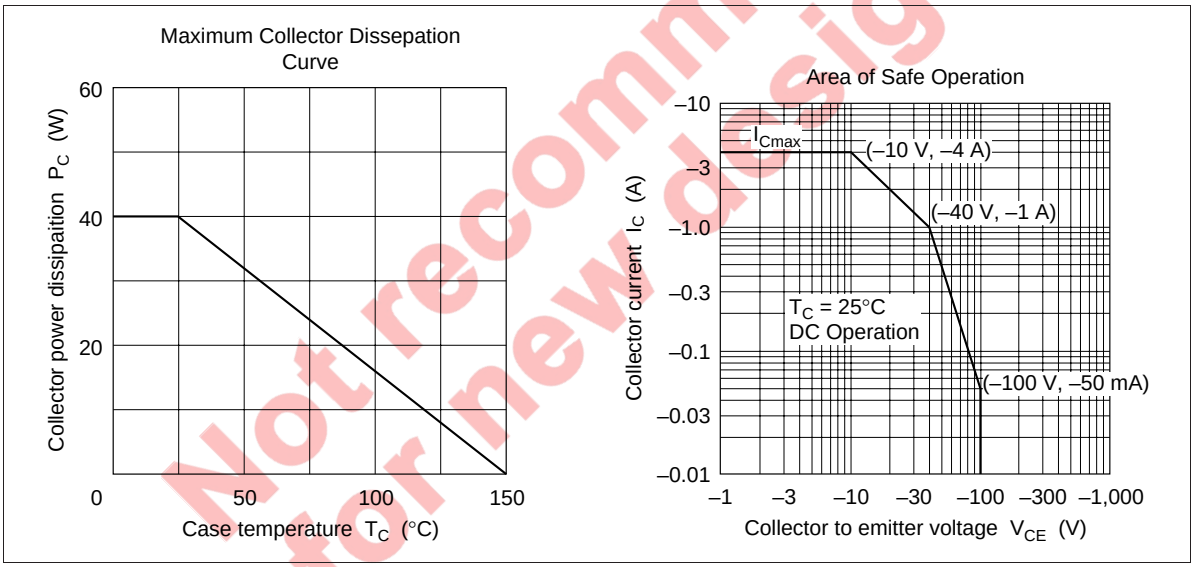
Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	–100	V
Collector to emitter voltage	V_{CEO}	–100	V
Emitter to base voltage	V_{EBO}	–4	V
Collector current	I_C	–4	A
Collector peak current	$I_{C(peak)}$	–5	A
Collector power dissipation	P_C	1.8	W
	P_C*[1]	40	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–45 to +150	°C

Note: 1. Value at T_C = 25°C

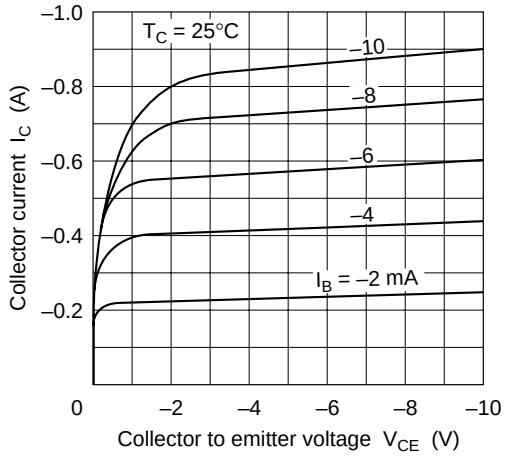
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	–100	—	—	V	I_C = –10 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	–4	—	—	V	I_E = –1 mA, I_C = 0
Collector cutoff current	I_{CEO}	—	—	–100	µA	V_{CE} = –80 V, R_{BE} = ∞
Emitter cutoff current	I_{EBO}	—	—	–50	µA	V_{EB} = –3.5 V, I_C = 0
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	–1.0	V	I_C = –1 A, I_B = –0.1 A*[1]
DC current transfer ratio	h_{FE}	50	—	250		V_{CE} = –4 V, I_C = –0.5 A*[1]
		25	—	350		I_C = –50 mA

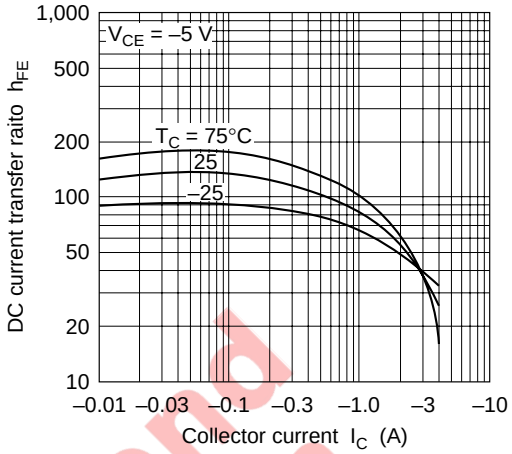
Note: 1. Pulse test



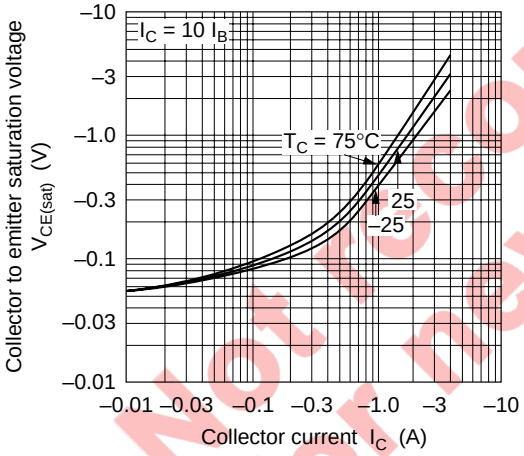
Typical Output Characteristics



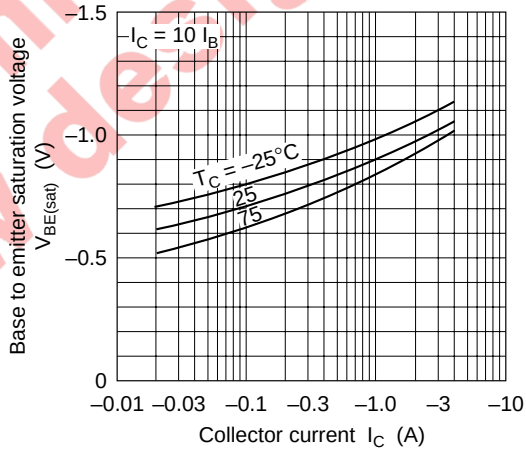
DC Current Transfer Ratio vs. Collector Current



Collector to Emitter Saturation Voltage vs. Collector Current



Base to Emitter Saturation Voltage vs. Collector Current



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